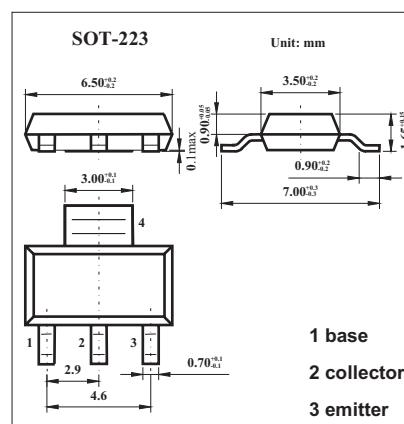


PNP Silicon Planar Medium Power High Gain Transistor FZT788B

■ Features

- Low equivalent on-resistance; $R_{CE(sat)}$ 93m Ω at 3A.
- Gain of 300 at $I_C=2$ Amps and Very low saturation voltage.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Continuous collector current	I_{CM}	-8	A
Peak pulse current	I_C	-3	A
Power dissipation	P_{tot}	2	W
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FZT788B

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA	-15			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =-10mA	-15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA	-5			V
Collector-base cut-off current	I _{CBO}	V _{CB} =-10V			-0.1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V			-0.1	μA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C =-0.5A, I _B =-2.5mA I _C =-1A, I _B =-5mA I _C =-2A, I _B =-10mA I _C =-3A, I _B =-50mA			-0.15 -0.25 -0.45 -0.5	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C =-1A, I _B =-5mA			-0.9	V
Base-emitter ON voltage *	V _{BE(on)}	I _C =-1A, V _{CE} =-2V		-0.75		V
Static Forward Current Transfer Ratio	h _{FE}	I _C =-10mA, V _{CE} =-2V *	500		1500	
		I _C =-1A, V _{CE} =-2V*	400			
		I _C =-2A, V _{CE} =-2V*	300			
		I _C =-6A, V _{CE} =-2V*	150			
Transitional frequency	f _T	I _C =-50mA, V _{CE} =-5V, f=50MHz	100			MHz
Input capacitance	C _{ibo}	V _{EB} =-0.5V, f=1MHz		225		pF
Output capacitance	C _{obo}	V _{CB} =-10V, f=1MHz		25		pF
Turn-on time	t _(on)	I _C =-500mA, V _{CC} =-10V		35		ns
Turn-off time	t _(off)	I _{B1} =I _{B2} =-50mA		400		ns

* Pulse test: t_p = 300 μs; d ≤ 0.02.

■ Marking

Marking	FZT788B
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